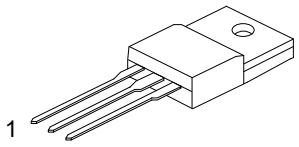
26NM60Z-U3

Preliminary ***Power MOSFET***

26A, 600V N-CHANNEL SUPER-JUNCTION MOSFET



TO-220F1

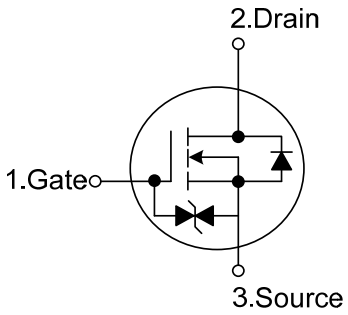
■ DESCRIPTION

The **UTC 26NM60Z-U3** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

■ FEATURES

* $R_{DS(ON)} \leq 0.14\ \Omega$ @ V_{GS}=10V, I_D=8.5A
* Fast switching capability
* Avalanche energy tested
* Improved dv/dt capability, high ruggedness
* With ESD Protected: HBM=2KV

■ SYMBOL



■ ORDERING INFORMATION

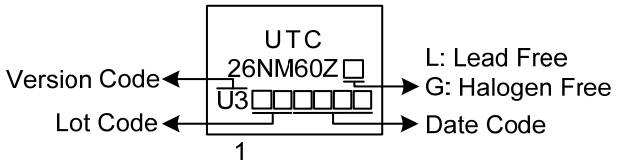
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
26NM60ZL-U3-TF1-T	26NM60ZG-U3-TF1-T	TO-220F1	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

26NM60ZG-U3-TF1-T

(1)Packing Type	(1) T: Tube
(2)Package Type	(2) TF1: TO-220F1
(3)Version Code	(3) Version U3
(4)Green Package	(4) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING


UTC
26NM60Z□
U3□□□□□□
Version Code
Lot Code
L: Lead Free
G: Halogen Free
Date Code
1

■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain-Source Voltage			V_{DSS}	600	V
Gate-Source Voltage			V_{GSS}	±20	V
Drain Current	Continuous	T_C=25°C	I_D	26	A
	Pulsed (Note 2)		I_{DM}	78	A
Avalanche Energy	Single Pulsed (Note 3)		E_{AS}	62.5	mJ
Peak Diode Recovery dv/dt (Note 4)			dv/dt	1.2	V/ns
Power Dissipation			P_D	33	W
Junction Temperature			T_J	+150	°C
Storage Temperature			T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 10mH, I_{AS} =3.5A, V_{DD} = 50V, R_G = 25Ω Starting T_J = 25°C
4. I_{SD} ≤ 26A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

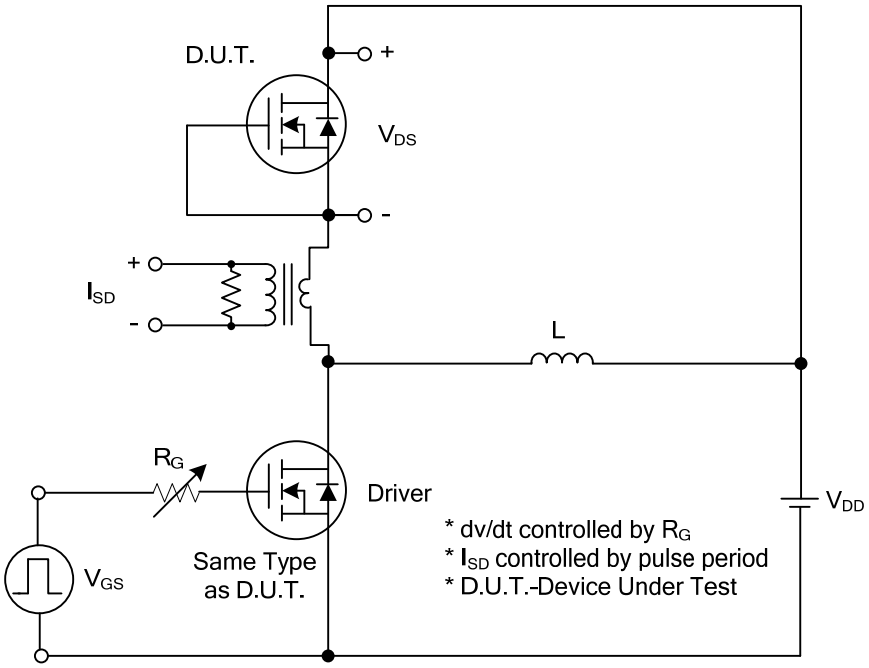
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62.5	°C/W
Junction to Case	θ_{JC}	3.79	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

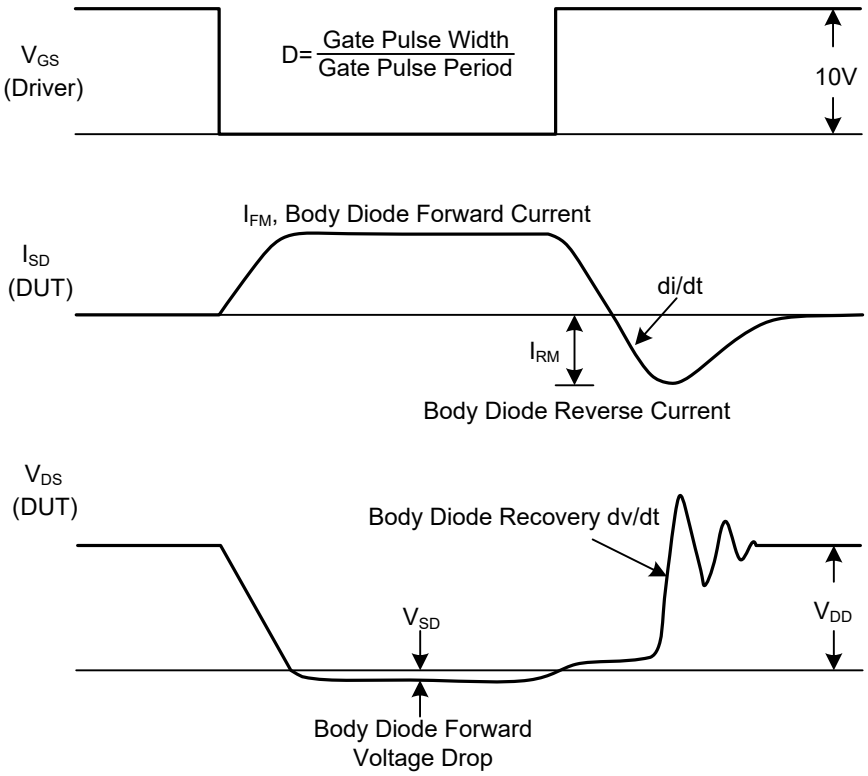
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	600			V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=600V, V_{GS}=0V			1	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V			±10	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.5		4.5	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=8.5A			0.14	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	V_{GS}=0V, V_{DS}=50V, f=1MHz		1400		pF
Output Capacitance	C_{OSS}			400		pF
Reverse Transfer Capacitance	C_{RSS}			14		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q_G	V_{DS}=480V, V_{GS}=10V, I_D=13A (Note 1, 2)		52		nC
Gate-Source Charge	Q_{GS}			11		nC
Gate-Drain Charge	Q_{DD}			27		nC
Turn-On Delay Time (Note 1)	$t_{D(ON)}$	V_{DD}=100V, V_{GS}=10V, I_D=13A, R_G=25Ω (Note 1, 2)		21		ns
Turn-On Rise Time	t_R			37		ns
Turn-Off Delay Time	$t_{D(OFF)}$			181		ns
Turn-Off Fall Time	t_F			77		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				26	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				78	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	I_S=26A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t_{rr}	I_S=26A, V_{GS}=0V, dI_F/dt=100A/μs		404		nS
Body Diode Reverse Recovery Charge	Q_{rr}			6155		nC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

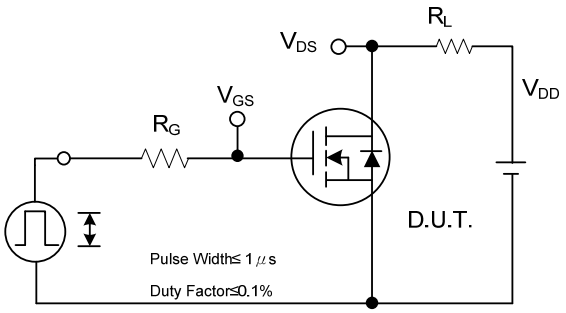


Peak Diode Recovery dv/dt Test Circuit

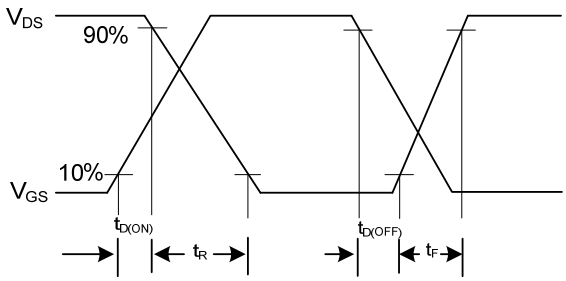


Peak Diode Recovery dv/dt Waveforms

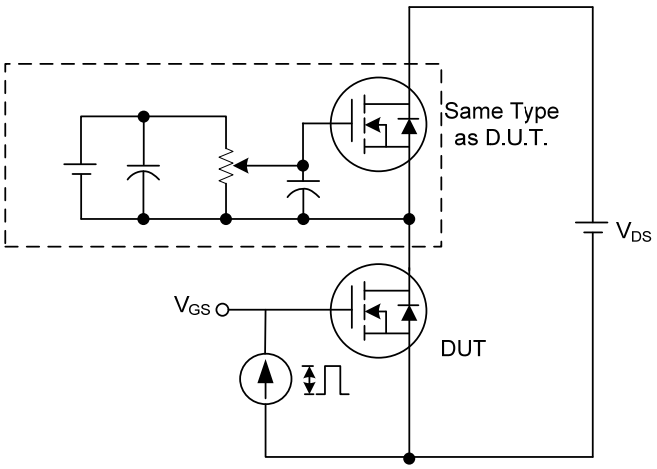
■ TEST CIRCUITS AND WAVEFORMS



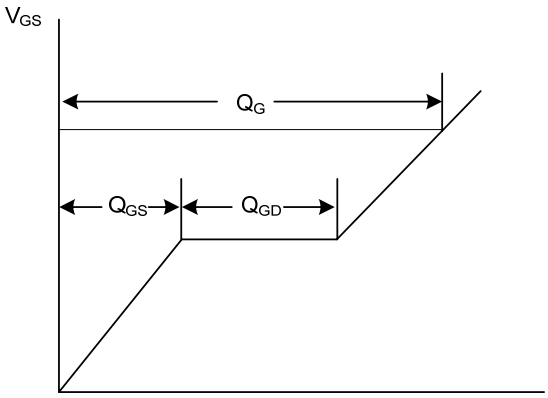
Switching Test Circuit



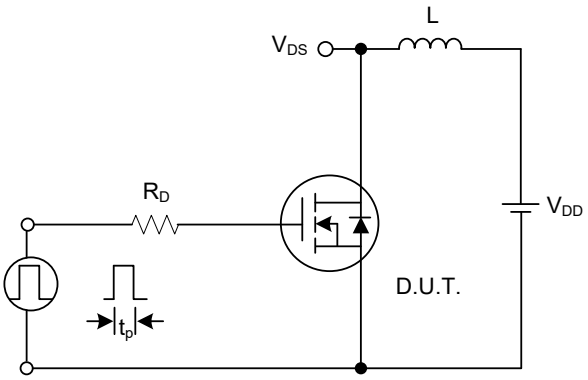
Switching Waveforms



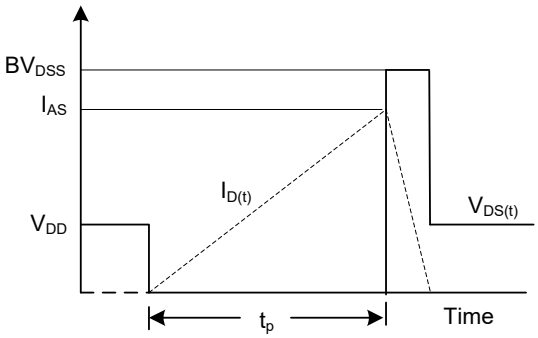
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms